Session- 2018-19

Field-Effect Transistors

Review

FETs vs. BJTs

Similarities:

Amplifiers
Switching devices
Impedance matching circuits

Differences:

FETs are voltage controlled devices. BJTs are current controlled devices.

FETs have higher input impedance (M-ohm). BJTs have higher gain.

FETs are less sensitive to temperature variations and are better suited for integrated circuits

Second breakdown

It is a failure mode in bipolar power transistors. In a power transistor with a large junction area, under certain conditions of current and voltage, the **current concentrates in a small spot of the base-emitter junction.** This causes local heating, progressing into a short between collector and emitter. This often leads to the destruction of the transistor. Secondary breakdown can occur both with forward and reverse base drive.

No such phenomenon in FET.

FET Types

JFET: Junction FET

MOSFET: Metal–Oxide–Semiconductor FET

D-MOSFET: Depletion MOSFET

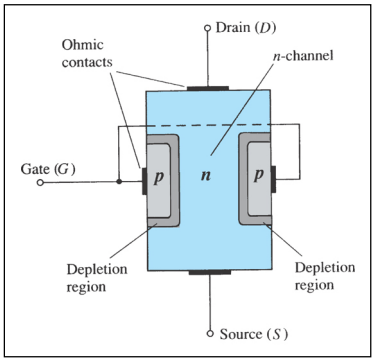
E-MOSFET: Enhancement MOSFET

JFET Construction

There are two types of JFETs:

***n*-channel**
***p*-channel**

The n-channel is the more widely used of the two.



JFETs have three terminals:

The **Drain** (D) and **Source** (S) are connected to the *n*-channel

The **Gate** (G) is connected to the *p*-type material

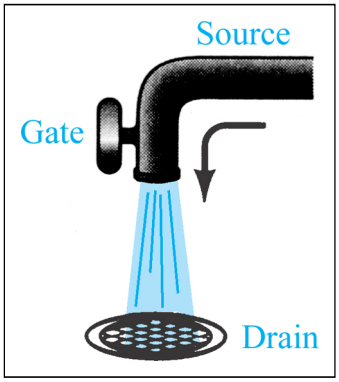
JFET Operation: The Basic Idea

JFET operation can be compared to that of a water spigot.

The **source** is the accumulation of electrons at the negative pole of the drain-source voltage.

The **drain** is the electron deficiency (or holes) at the positive pole of the applied voltage.

The **gate** controls the width of the n-channel and, therefore, the flow of charges from source to drain.



JFET Operating Characteristics

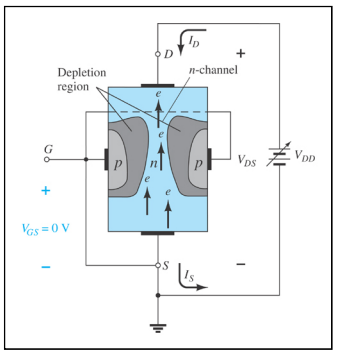
There are three basic operating conditions for a JFET:

- V_{GS} = 0 V, V_{DS} increasing to some positive value
- V_{GS} < 0 V, V_{DS} at some positive value
- Voltage-controlled resistor

JFET Characteristics: V_{GS}=0V

Three things happen when V_{GS} = 0 V and V_{DS} increases from 0 V to a more positive voltage:

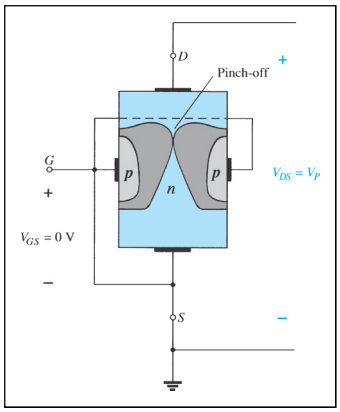
- The size of the depletion region between *p*- type gate and *n*-channel increases.
- Increasing the size of the depletion region decreases the width of the *n*-channel, which increases its resistance.
- Even though the *n*-channel resistance is increasing, the current from source to drain (I_D) through the *n*-channel is increasing because V_{DS} is increasing.



JFET Characteristics: Pinch Off

• If V_{GS} = 0 V and V_{DS} continually increases to a more positive voltage, a point is reached where the depletion region gets so large that it pinches off the channel.

• This suggests that the current in channel (I_D) drops to 0 A, but it does not: As V_{DS} increases, so does I_D. However, once pinch off occurs, further increases in V_{DS} do not cause I_D to increase.

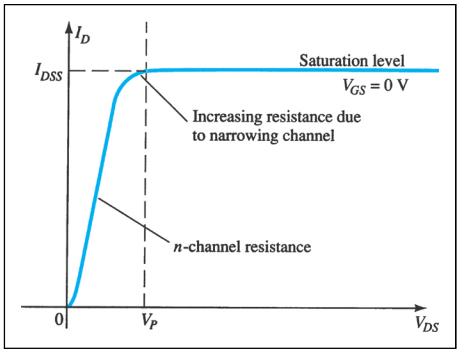


JFET Characteristics: Saturation

At the pinch-off point:

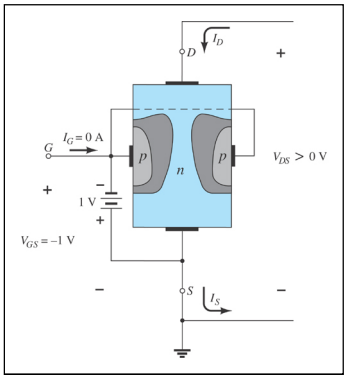
Any further increase in V_{DS} does not produce any increase in I_D. V_{DS} at pinch-off is denoted as $\boldsymbol{V_p}$

I_D is at saturation or maximum, and is referred to as $\boldsymbol{I_{DSS}}$.



JFET Operating Characteristics

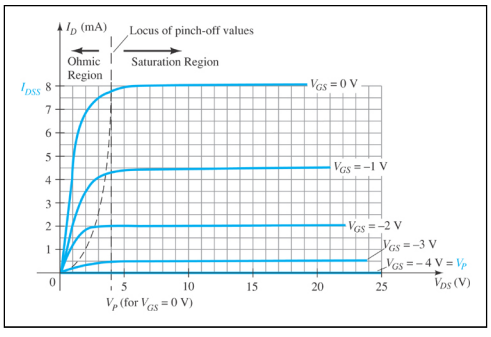
As V_{GS} becomes more negative, the depletion region increases.



JFET Operating Characteristics

As V_{GS} becomes more negative:

- The JFET experiences pinch-off at a lower voltage (V_P).
- I_D decreases ($I_D < I_{DSS}$) even when V_{DS} increases
- I_D eventually drops to 0 A. The value of V_{GS} that causes this to occur is designated ***$V_{GS(off)}$***.



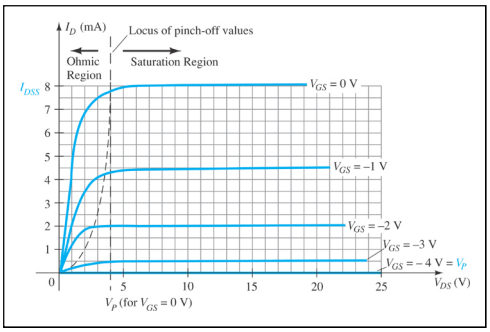
Note that at high levels of V_{DS} the JFET reaches a breakdown situation. I_D increases uncontrollably if $V_{DS} > V_{DSmax}$, and the JFET is likely destroyed.

Voltage-Controlled Resistor

The region to the left of the pinch-off point is called the **ohmic region.**

The JFET can be used as a variable resistor, where V_{GS} controls the drain-source resistance (r_d).

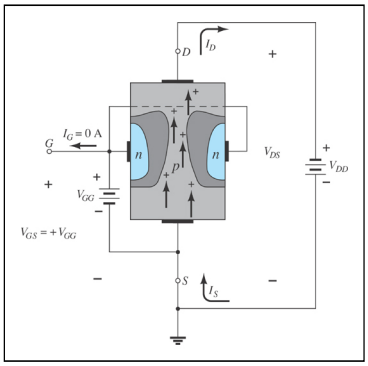
$$r_d = \frac{r_o}{\left(1 - \frac{V_{GS}}{V_P}\right)^2}$$



As V_{GS} becomes more negative, the resistance (r_d) increases.

P-Channel JFETs

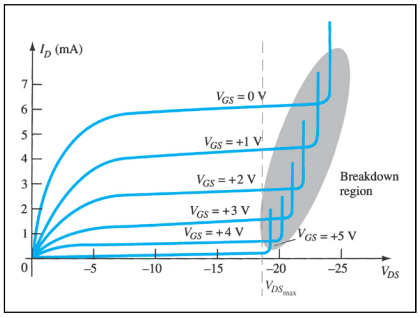
The *p*-channel JFET behaves the same as the *n*-channel JFET. The only differences are that the voltage polarities and current directions are reversed.



P-Channel JFET Characteristics

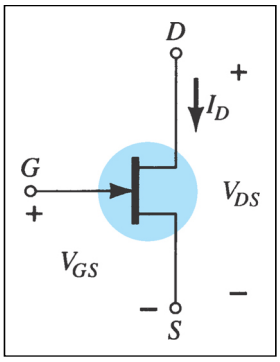
As V_{GS} becomes more positive:

- The JFET experiences pinch-off at a lower voltage (V_P).
- The depletion region increases, and I_D decreases ($I_D < I_{DSS}$)
- I_D eventually drops to 0 A (when $V_{GS} = V_{GSoff}$)



Also note that at high levels of V_{DS} the JFET reaches a breakdown situation: I_D increases uncontrollably if $V_{DS} > V_{DSmax}$.

N-Channel JFET Symbol



JFET Transfer Characteristics

JFET input-to-output transfer characteristics are not as straightforward as they are for a BJT.

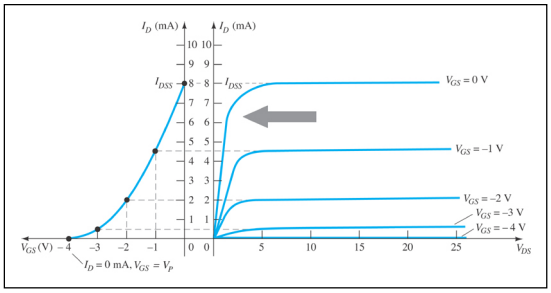
• BJT: β indicates the relationship between I_B (input) and I_C (output).

• JFET: The relationship of V_{GS} (input) and I_D (output) is a little more complicated:

$$I_D = I_{DSS}\left(1-\frac{V_{GS}}{V_P}\right)^2$$

JFET Transfer Curve

This graph shows the value of I_D for a given value of V_{GS}.



Plotting the JFET Transfer Curve

Using I_{DSS} and V_p ($V_{GS(off)}$) values found in a specification sheet, the transfer curve can be plotted according to these three steps:

1. Solving for V_{GS} = 0 V: $I_D = I_{DSS}$
2. Solving for $V_{GS} = V_{GS(off)}$: I_D = 0 A

$$I_D = I_{DSS}\left(1-\frac{V_{GS}}{V_P}\right)^2$$

3. Solving for V_{GS} = 0 V to $V_{GS(off)}$: 0 A < I_D < I_{DSS}

JFET Specification Sheet

Electrical Characteristics

ELECTRICAL CHARACTERISTICS T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min	Typ	Max	Units
OFF CHARACTERISTICS							
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	I_G = 10 µA, V_{DS} = 0		–25			V
I_{GSS}	Gate Reverse Current	V_{GS} = –15 V, V_{DS} = 0 V_{GS} = –15 V, V_{DS} = 0, T_A = 100°C				–1.0 –200	nA nA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	V_{DS} = 15 V, I_D = 10 nA	5457	–0.5		–6.0	V
V_{GS}	Gate-Source Voltage	V_{DS} = 15 V, I_D = 100 µA	5457		–2.5		V
ON CHARACTERISTICS							
I_{DSS}	Zero-Gate Voltage Drain Current	V_{DS} = 15 V, V_{GS} = 0	5457	1.0	3.0	5.0	mA
SMALL SIGNAL CHARACTERISTICS							
g_{fs}	Forward Transfer Conductance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz	5457	1000		5000	µmhos
g_{os}	Output Conductance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz			10	50	µmhos
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz			4.5	7.0	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz			1.5	3.0	pF
NF	Noise Figure	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz, R_G = 1.0 megohm, BW = 1.0 Hz				3.0	dB

JFET Specification Sheet

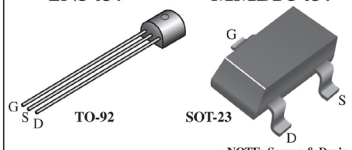
Maximum Ratings

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	25	V
V_{DG}	Drain-Gate Voltage	25	V
V_{GS}	Gate-Source Voltage	–25	V
I_{GF}	Forward Gate Current	10	mA
T_j, T_{stg}	Operating and Storage Junction Temperature Range	–55 to +150	°C

FAIRCHILD
SEMICONDUCTOR ™

2N5457 **MMBF5457**



NOTE: Source & Drain are interchangeable

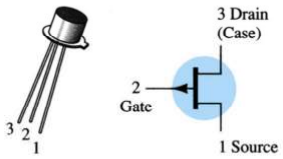
N-Channel General Purpose Amplifier

This device is a low-level audio amplifier and switching transistor, and can be used for analog switching applications.

Case and Terminal Identification

2N2844

CASE 22-03, STYLE 12
TO-18 (TO-206AA)



JFETs
GENERAL PURPOSE
P-CHANNEL

Testing JFETs

Curve Tracer

A curve tracer displays the I_D versus V_{DS} graph for various levels of V_{GS}.

Specialized FET Testers

These testers show I_{DSS} for the JFET under test.

METAL-OXIDE-SEMICONDUCTOR-FIELD-EFFECT TRANSISTOR (MOSFETs)

MOSFETs have characteristics similar to those of JFETs and additional characteristics that make them very useful.

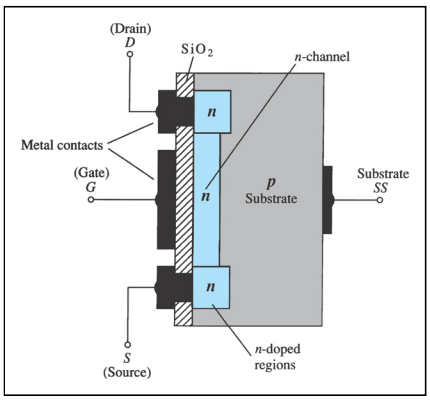
There are two types of MOSFETs:

- **Depletion-Type**
- **Enhancement-Type**

Depletion-Type MOSFET Construction

The **Drain (D)** and **Source (S)** connect to the to *n*-type regions. These *n*-typed regions are connected via an *n*-channel. This *n*-channel is connected to the **Gate (G)** via a thin insulating layer of silicon dioxide (SiO_2).

The *n*-type material lies on a *p*-type substrate that may have an additional terminal connection called the **Substrate (SS)**.

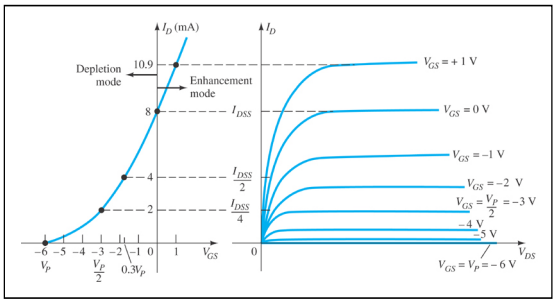


Basic MOSFET Operation

A depletion-type MOSFET can operate in two modes:

Depletion mode

Enhancement mode

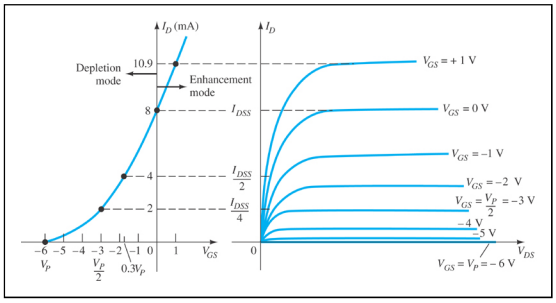


Depletion Mode Operation (D-MOSFET)

The characteristics are similar to a JFET.

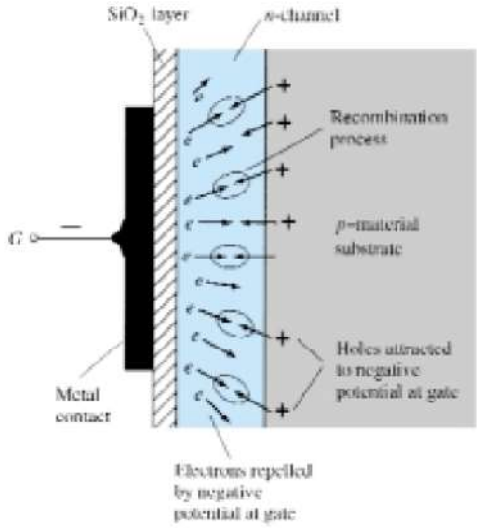
When $V_{GS} = 0$ V, $I_D = I_{DSS}$

When $V_{GS} < 0$ V, $I_D < I_{DSS}$



The formula used to plot the transfer curve for a JFET applies to a D-MOSFET as well:

$$I_D = I_{DSS}\left(1 - \frac{V_{GS}}{V_P}\right)^2$$

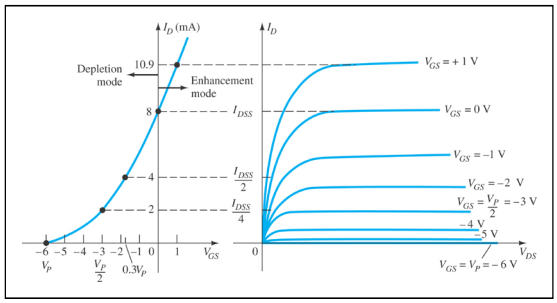


Enhancement Mode Operation (D-MOSFET)

$V_{GS} > 0$ V, I_D increases above I_{DSS} ($I_D > I_{DSS}$)

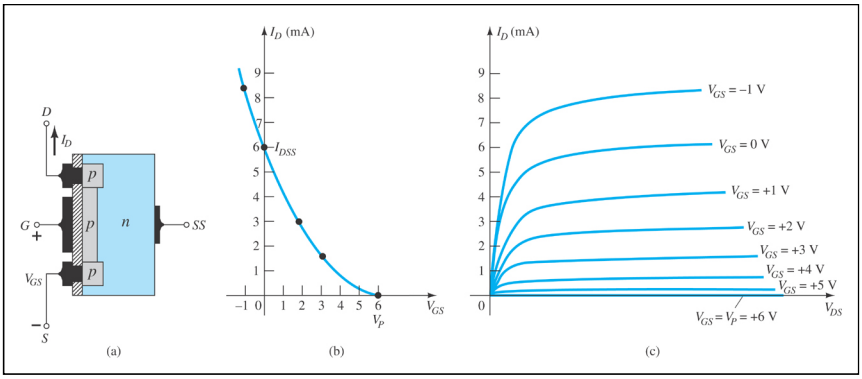
The formula used to plot the transfer curve still applies:

$$I_D = I_{DSS}\left(1 - \frac{V_{GS}}{V_P}\right)^2$$

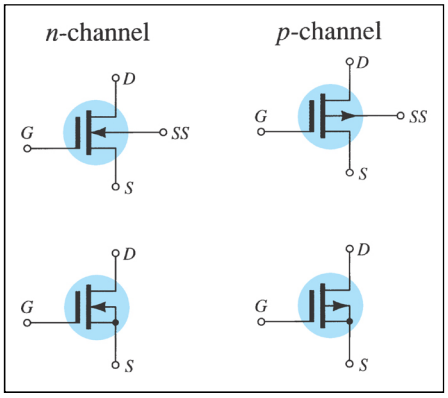


Note that V_{GS} is now positive

p-Channel D-Type MOSFET



D-Type MOSFET Symbols



Specification Sheet

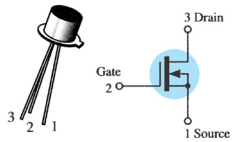
Maximum Ratings

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain–Source Voltage 2N3797	V_{DS}	20	Vdc
Gate–Source Voltage	V_{GS}	±10	Vdc
Drain Current	I_D	20	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	200 1.14	mW mW/°C
Junction Temperature Range	T_J	+175	°C
Storage Channel Temperature Range	T_{stg}	–65 to +200	°C

2N3797

MOSFET
LOW–POWER AUDIO



N-CHANNEL – DEPLETION

Specification Sheet

Electrical Characteristics

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain Source Breakdown Voltage (V_{GS} = −7.0 V, I_D = 5.0 μA)	2N3797	$V_{(BR)DSX}$	20	25	–	Vdc
Gate Reverse Current (1) (V_{GS} = −10 V, V_{DS} = 0) (V_{GS} = −10 V, V_{DS} = 0, T_A = 150°C)		I_{GSS}	– –	– –	1.0 200	pAdc
Gate Source Cutoff Voltage (I_D = 2.0 μA, V_{DS} = 10 V)	2N3797	$V_{GS(off)}$	–	−5.0	−7.0	Vdc
Drain-Gate Reverse Current (1) (V_{DG} = 10 V, I_S = 0)		I_{DGO}	–	–	1.0	pAdc
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current (V_{DS} = 10 V, V_{GS} = 0)	2N3797	I_{DSS}	2.0	2.9	6.0	mAdc
On-State Drain Current (V_{DS} = 10 V, V_{GS} = +3.5 V)	2N3797	$I_{D(on)}$	9.0	14	18	mAdc
SMALL-SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (V_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz)	2N3797	$\|Y_{fs}\|$	1500	2300	3000	μmhos
(V_{DS} = 10 V, V_{GS} = 0, f = 1.0 MHz)	2N3797		1500	–	–	
Output Admittance (I_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz)	2N3797	$\|Y_{os}\|$	–	27	60	μmhos
Input Capacitance (V_{DS} = 10 V, V_{GS} = 0, f = 1.0 MHz)	2N3797	C_{iss}	–	6.0	8.0	pF
Reverse Transfer Capacitance (V_{DS} = 10 V, V_{GS} = 0, f = 1.0 MHz)		C_{rss}	–	0.5	0.8	pF
FUNCTIONAL CHARACTERISTICS						
Noise Figure (V_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz, R_S = 3 megohms)		NF	–	3.8	–	dB

(1) This value of current includes both the FET leakage current as well as the leakage current associated with the test socket and fixture when measured under best attainable conditions.

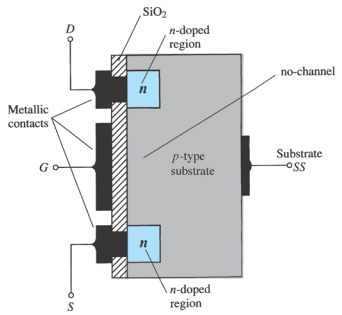
E-Type MOSFET Construction

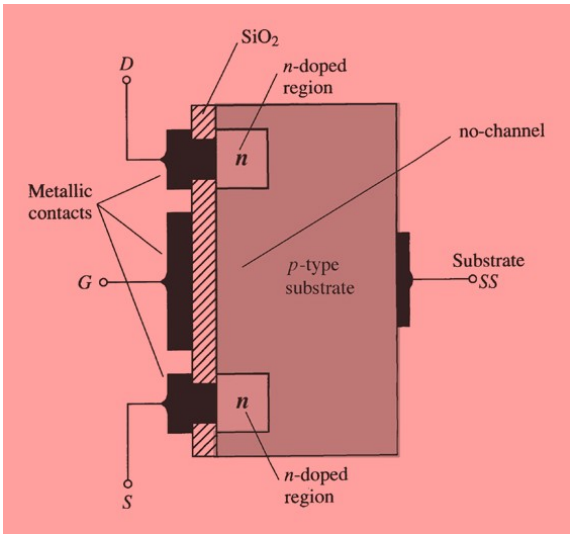
The **Drain (D)** and **Source (S)** connect to the to *n*-type regions. These *n*-type regions are connected via an *n*-channel

The **Gate (G)** connects to the *p*-type substrate via a thin insulating layer of silicon dioxide (SiO_2)

There is no channel

The *n*-type material lies on a *p*-type substrate that may have an additional terminal connection called the **Substrate (SS)**





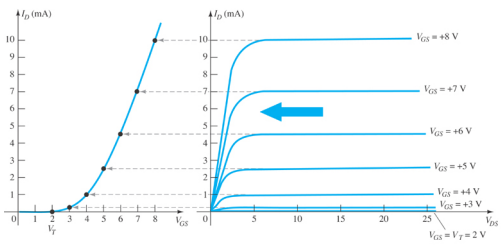
E-Type MOSFET Operation

The enhancement-type MOSFET (E-MOSFET) operates only in the enhancement mode.

V_{GS} is always positive

As V_{GS} increases, I_D increases

As V_{GS} is kept constant and V_{DS} is increased, then I_D saturates (I_{DSS}) and the saturation level (V_{DSsat}) is reached



E-Type MOSFET Transfer Curve

To determine I_D given V_{GS}:

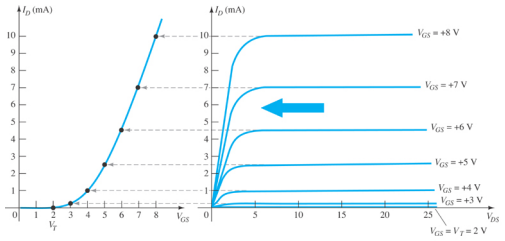
$$I_D = k(V_{GS} - V_T)^2$$

where:

V_T = the E-MOSFET threshold voltage

k, a constant, can be determined by using values at a specific point and the formula:

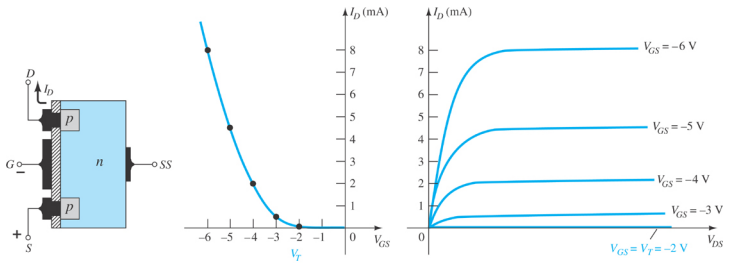
$$k = \frac{I_{D(ON)}}{(V_{GS(ON)} - V_T)^2}$$



V_{DSsat} can be calculated using:

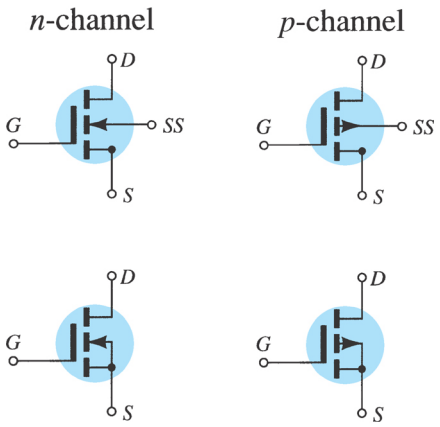
$$V_{DSsat} = V_{GS} - V_T$$

p-Channel E-Type MOSFETs



The *p*-channel enhancement-type MOSFET is similar to its *n*-channel counterpart, except that the voltage polarities and current directions are reversed.

MOSFET Symbols



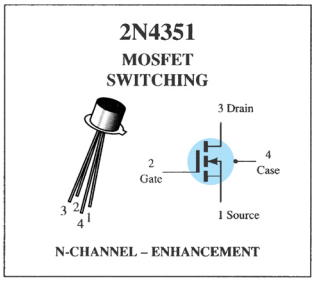
Specification Sheet

Maximum Ratings

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DS}	25	Vdc
Drain–Gate Voltage	V_{DG}	30	Vdc
Gate–Source Voltage*	V_{GS}	30	Vdc
Drain Current	I_D	30	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	300 1.7	mW mW/°C
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{stg}	–65 to +175	°C

* Transient potentials of ± 75 Volt will not cause gate-oxide failure.



more…

Specification Sheet

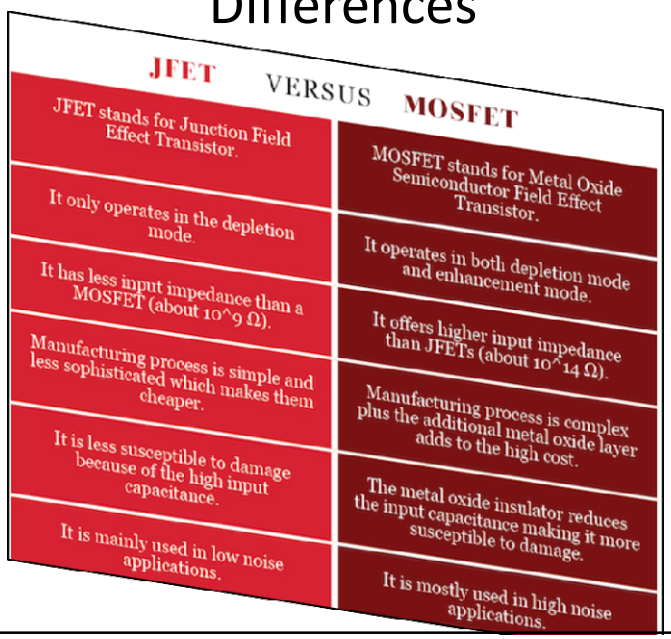
Electrical Characteristics

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Drain-Source Breakdown Voltage (I_D = 10 μA, V_{GS} = 0)	$V_{(BR)DSX}$	25	–	Vdc
Zero-Gate-Voltage Drain Current (V_{DS} = 10 V, V_{GS} = 0) T_A = 25°C / T_A = 150°C	I_{DSS}	– / –	10 / 10	nAdc / μAdc
Gate Reverse Current (V_{GS} = ± 15 Vdc, V_{DS} = 0)	I_{GSS}	–	± 10	pAdc
ON CHARACTERISTICS				
Gate Threshold Voltage (V_{DS} = 10 V, I_D = 10 μA)	$V_{GS(Th)}$	1.0	5	Vdc
Drain-Source On-Voltage (I_D = 2.0 mA, V_{GS} = 10V)	$V_{DS(on)}$	–	1.0	V
On-State Drain Current (V_{GS} = 10 V, V_{DS} = 10 V)	$I_{D(on)}$	3.0	–	mAdc
SMALL-SIGNAL CHARACTERISTICS				
Forward Transfer Admittance (V_{DS} = 10 V, I_D = 2.0 mA, f = 1.0 kHz)	$\|y_{fs}\|$	1000	–	μmho
Input Capacitance (V_{DS} = 10 V, V_{GS} = 0, f = 140 kHz)	C_{iss}	–	5.0	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = 0, f = 140 kHz)	C_{rss}	–	1.3	pF
Drain-Substrate Capacitance ($V_{DS(SUB)}$ = 10 V, f = 140 kHz)	$C_{d(sub)}$	–	5.0	pF
Drain-Source Resistance (V_{GS} = 10 V, I_D = 0, f = 1.0 kHz)	$r_{ds(on)}$	–	300	ohms
SWITCHING CHARACTERISTICS				
Turn-On Delay (Fig. 5)	t_{d1}	–	45	ns
Rise Time (Fig. 6)	t_r	–	65	ns
Turn-Off Delay (Fig. 7)	t_{d2}	–	60	ns
Fall Time (Fig. 8)	t_f	–	100	ns

(I_D = 2.0 mAdc, V_{DS} = 10 Vdc, (V_{GS} = 10 Vdc) (See Figure 9; Times Circuit Determined))

Differences



Handling MOSFETs

MOSFETs are very sensitive to static electricity.

Because of the very thin SiO_2 layer between the external terminals and the layers of the device, any small electrical discharge can create an unwanted conduction.

Protection

- Always transport in a static sensitive bag
- Always wear a static strap when handling MOSFETS
- Apply voltage limiting devices between the gate and source, such as back-to-back Zeners to limit any transient voltage.

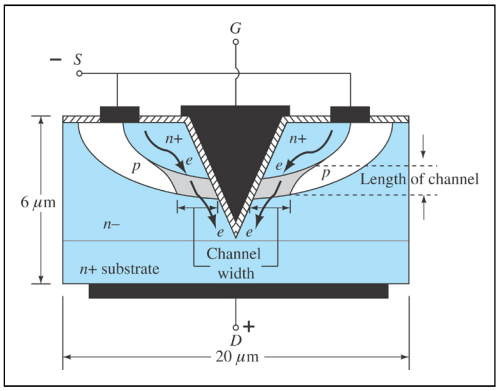
VMOS Devices

VMOS (vertical MOSFET) is a component structure that provides greater surface area.

Advantages

VMOS devices handle higher currents by providing more surface area to dissipate the heat.

VMOS devices also have faster switching times.

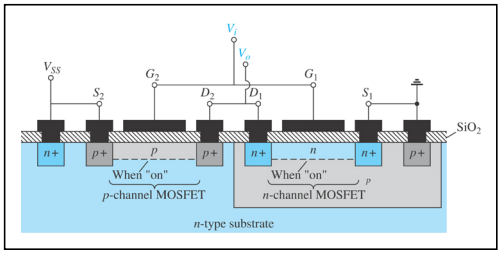


CMOS Devices

CMOS (complementary MOSFET) uses a p-channel and n-channel MOSFET; often on the same substrate as shown here.

Advantages

- Useful in logic circuit designs
- Higher input impedance
- Faster switching speeds
- Lower operating power levels



Summary Table